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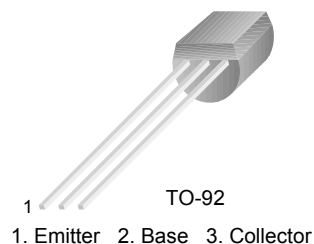
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2N6517

NPN Epitaxial Silicon Transistor

Features

- High Voltage Transistor
- Collector Dissipation: $P_C(\text{max}) = 625\text{mW}$
- Complement to 2N6520
- Suffix “-C” means Center Collector (1. Emitter 2. Collector 3. Base)



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|-----------------------------|-----------|------------------|
| V_{CBO} | Collector-Base Voltage | 2N6517 | 350 |
| | | 2N6517C | 400 |
| V_{CEO} | Collector-Emitter Voltage | 2N6517 | 350 |
| | | 2N6517C | 400 |
| V_{EBO} | Emitter-Base Voltage | 6 | V |
| I_C | Collector Current | 500 | mA |
| P_C | Collector Power Dissipation | 625 | mW |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -55 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Max. | Units |
|------------|---------------------------------------|--|------|------|-------|
| BV_{CBO} | Collector-Base Breakdown Voltage | 2N6517 $I_C = 100\mu\text{A}, I_E = 0$ | 350 | | V |
| | | 2N6517C $I_C = 100\mu\text{A}, I_E = 0$ | 400 | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage * | 2N6517 $I_C = 1\text{mA}, I_B = 0$ | 350 | | V |
| | | 2N6517C $I_C = 1\text{mA}, I_B = 0$ | 400 | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = 10\mu\text{A}, I_C = 0$ | 6 | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 250\text{V}, I_E = 0$ | | 50 | nA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 5\text{V}, I_C = 0$ | | 50 | nA |
| h_{FE} | DC Current Gain * | 2N6517/2N6517C $V_{CE} = 10\text{V}, I_C = 1\text{mA}$ | 20 | | |
| | | 2N6517/2N6517C $V_{CE} = 10\text{V}, I_C = 10\text{mA}$ | 30 | | |
| | | 2N6517/2N6517C $V_{CE} = 10\text{V}, I_C = 30\text{mA}$ | 30 | 200 | |
| | | 2N6517/2N6517C $V_{CE} = 10\text{V}, I_C = 50\text{mA}$ | 20 | 200 | |
| | | 2N6517/2N6517C $V_{CE} = 10\text{V}, I_C = 100\text{mA}$ | 15 | | |
| | | 2N6517C $V_{CE} = 10\text{V}, I_C = 5\text{mA}$ | 50 | 200 | |

Electrical Characteristics (Continued) $T_a = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Max. | Units |
|---------------|--------------------------------------|--|------|------|-------|
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 10\text{mA}, I_B = 1\text{mA}$ | | 0.3 | V |
| | | $I_C = 20\text{mA}, I_B = 2\text{mA}$ | | 0.35 | V |
| | | $I_C = 30\text{mA}, I_B = 3\text{mA}$ | | 0.5 | V |
| | | $I_C = 50\text{mA}, I_B = 5\text{mA}$ | | 1 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = 10\text{mA}, I_B = 1\text{mA}$ | | 0.75 | V |
| | | $I_C = 20\text{mA}, I_B = 2\text{mA}$ | | 0.85 | V |
| | | $I_C = 30\text{mA}, I_B = 3\text{mA}$ | | 0.9 | V |
| C_{ob} | Output Capacitance | $V_{CB} = 20\text{V}, I_E = 0, f = 1\text{MHz}$ | | 6 | pF |
| f_T | Current Gain Bandwidth Product * | $I_C = 10\text{mA}, V_{CE} = 20\text{V}, f = 20\text{MHz}$ | 40 | 200 | MHz |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $I_C = 100\text{mA}, V_{CE} = 10\text{V}$ | | 2 | V |

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

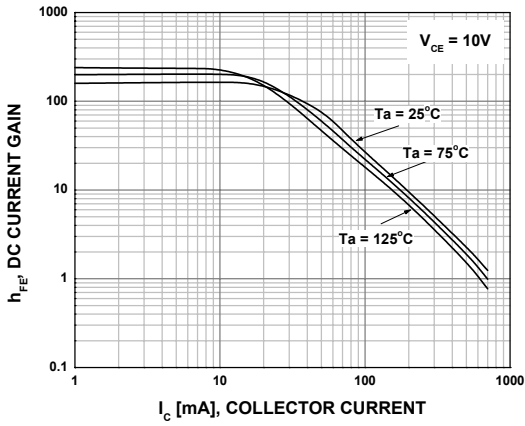


Figure 1. DC Current Gain

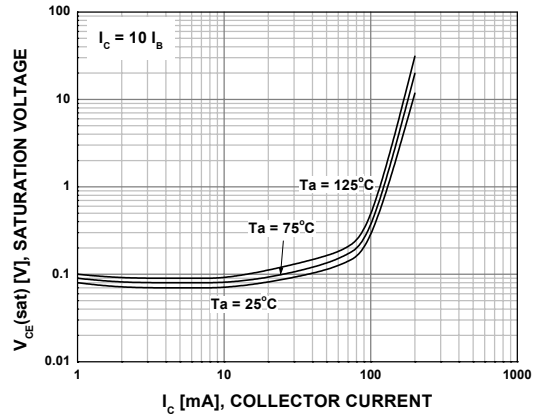


Figure 2. Saturation Voltage

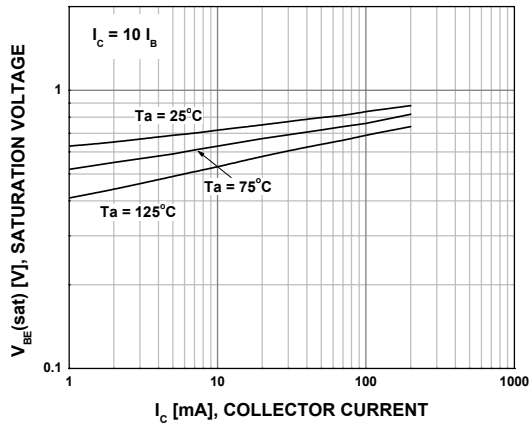


Figure 3. Saturation Voltage

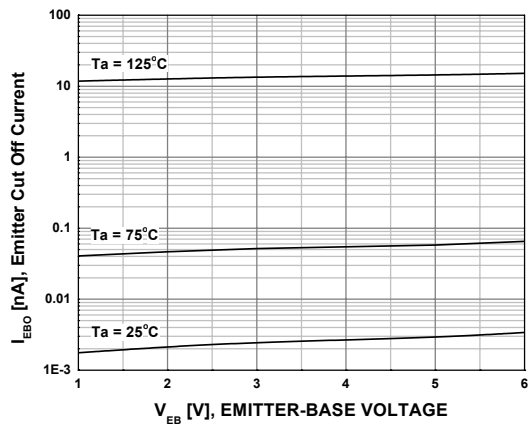


Figure 4. Emitter Cut Off Current

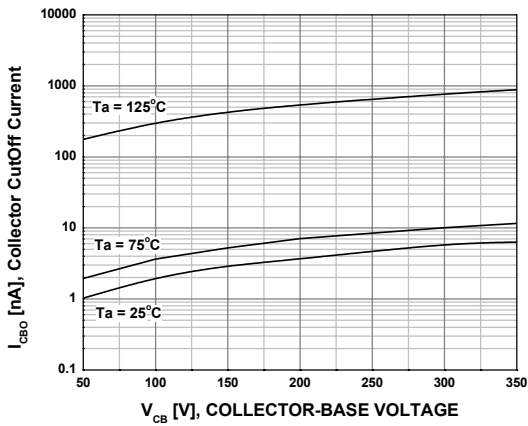


Figure 5. Collector CutOff Current

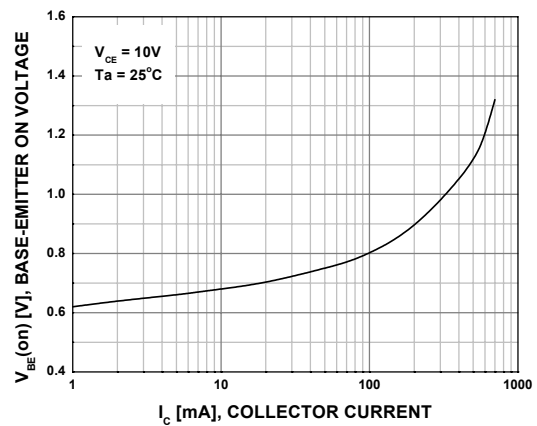


Figure 6. Base-Emitter On Voltage

Typical Performance Characteristics (Continued)

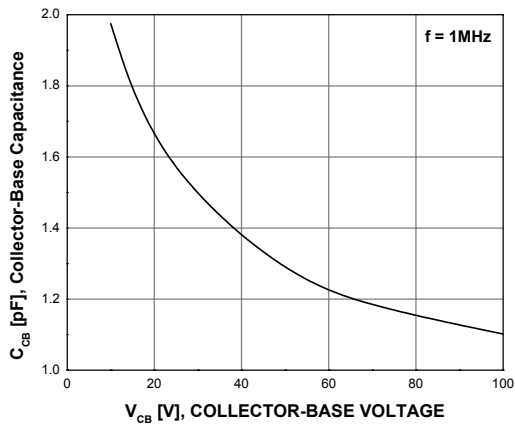


Figure 7. Output Capacitance

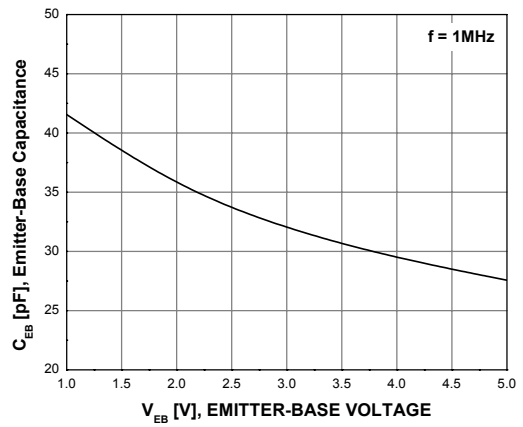


Figure 8. Input Capacitance

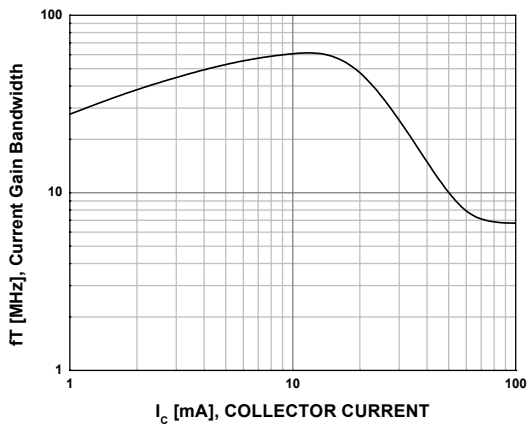


Figure 9. Current Gain Bandwidth Product

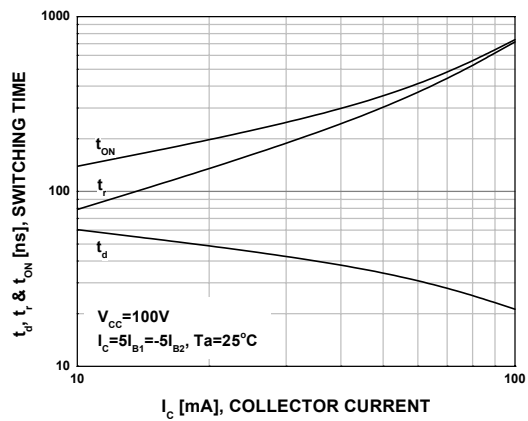


Figure 10. Resistive Load Switching

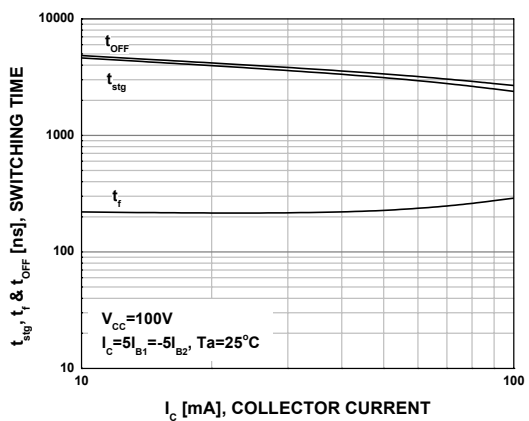
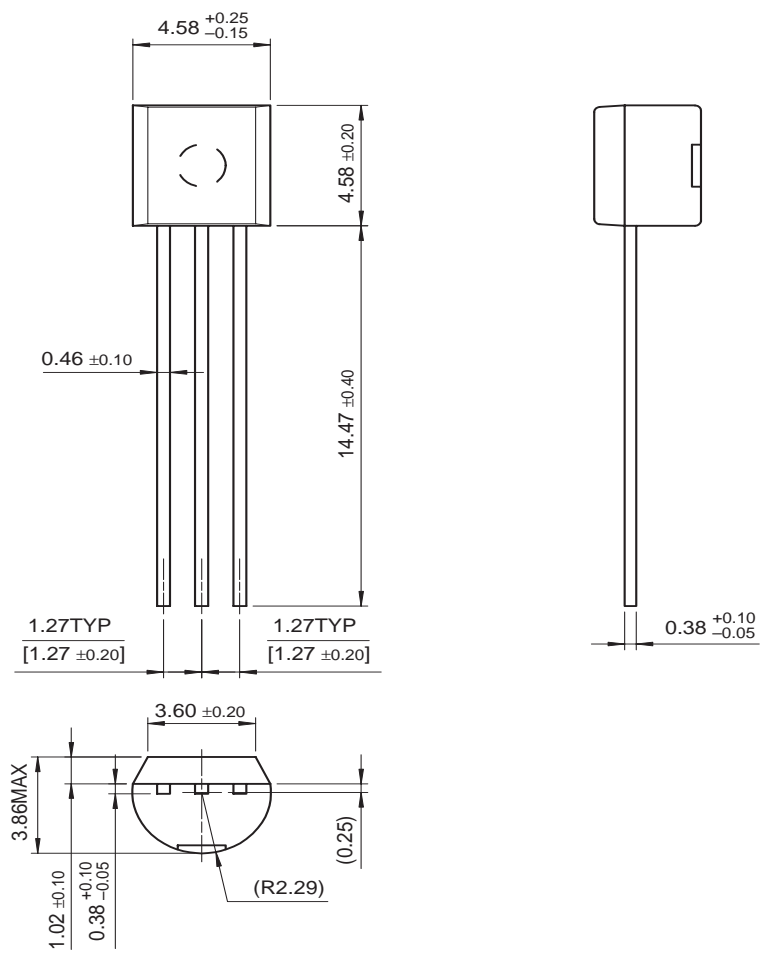


Figure 11. Resistive Load Switching

Physical Dimensions

TO-92



Dimensions in Millimeters



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